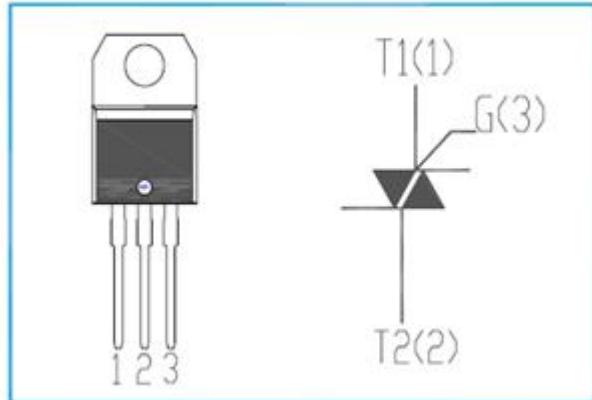


**FEATURES**

- With TO-220 package
- Glass passivated triacs in a plastic envelope, Intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all our quadrants.
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


**ABSOLUTE MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	PARAMETER	MIN	UNIT
$V_{DRM}$	Repetitive peak off-state voltage	800	V
$V_{RRM}$	Repetitive peak off-state voltage	800	V
$I_{T(RMS)}$	RMS on-state current (full sine wave)	12	A
$I_{TSM}$	Non-repetitive peak on-state current	95	A
$P_{GM}$	Peak gate power dissipation	5	W
$P_{G(AV)}$	Average gate power dissipation	0.5	W
$T_j$	Operating junction temperature	125	°C
$T_{stg}$	Storage temperature	-45~150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise specified)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$I_{RRM}$	Repetitive peak reverse current	$V_R=V_{RRM}$ , $V_R=V_{RRM}$ , $T_j=125^\circ\text{C}$	0.02 0.5		mA
$I_{DRM}$	Repetitive peak off-state current	$V_D=V_{DRM}$ , $V_D=V_{DRM}$ , $T_j=125^\circ\text{C}$	0.02 0.5		mA
$I_{GT}$	Gate trigger current	I	5	mA	
		II	5		
		III	5		
		IV	10		
$V_{TM}$	On-state voltage	$I_T = 15\text{A}$		1.65	V
$I_H$	Holding current	$I_{GT} = 0.1\text{A}$ , $V_D = 12\text{V}$		35	mA
$V_{GT}$	Gate trigger voltage	$V_D = 12\text{V}$ ; $R_L = 30\ \Omega$ all quadrant		1.5	V